

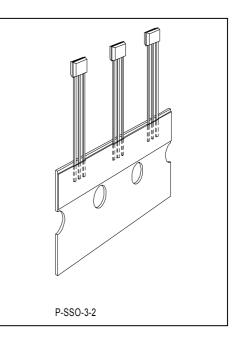
# High Precision Hall-Effect Switch

TLE4946-1L

Data Sheet Version 1.0 2004-03-04

#### Features

- 2.7V to 24V supply voltage operation
- Operation from unregulated power supply
- High sensitivity and high stability of the magnetic switching points
- High resistance to mechanical stress by Active Error Compensation
- Reverse battery protection (-18V)
- Superior temperature stability
- Peak temperatures up to 195°C without damage
- Low jitter (typ. 1µs)
- High ESD performance (±6kV HBM)
- Digital output signal
- Unipolar version
- Leaded package P-SSO-3-2



Туре	Ordering Code	Package
TLE4946-1L	Q62705-K0733	P-SSO-3-2

#### **Functional Description**

The TLE4946-1L is an integrated circuit Hall-effect sensor designed specifically for highly accurate automotive and industrial applications. Precise magnetic switching points and high temperature stability are achieved by active compensation circuits and chopper techniques on chip.



#### **Circuit Description**

The chopped Hall IC Switch comprises a Hall probe, bias generator, compensation circuits, oscillator and output transistor.

The bias generator provides currents for the Hall probe and the active circuits. Compensation circuits stabilize the temperature behavior and reduce technology variations.

The Active Error Compensation rejects offsets in signal stages and the influence of mechanical stress to the Hall probe caused by molding and soldering processes and other thermal stresses in the package. This chopper technique together with the threshold generator and the comparator ensure high accurate magnetic switching points.

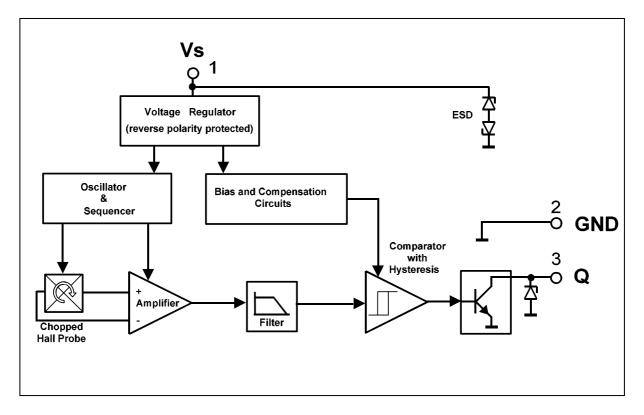


Figure 1: Block Diagram



## **Pin Configurations**

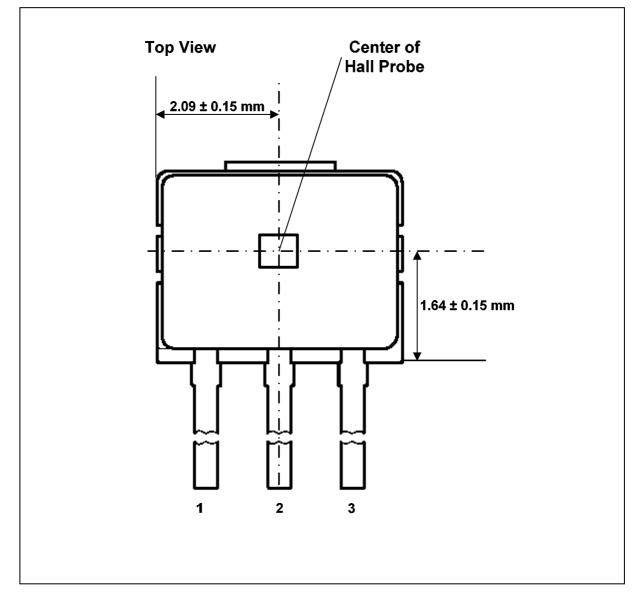


Figure 2: Pin Configuration

### **Pin Definition and Functions**

Pin	Symbol	Function
1	Vs	Supply voltage
2	GND	Ground
3	Q	Output





#### **Absolute Maximum Ratings**

Tj = -40 to 150°C

Parameter	Symbol	min.	max.	Unit	Conditions
Supply Voltage	Vs	-18	18	V	
	_	-18	24		for 1h ,Rs>=200 Ohm
		-18	26		for 5min, Rs>=200 Ohm
Supply Current through	I <sub>S</sub>	-50	+50	mA	
protection device					
Output Voltage	$V_{Q}$	-0.7	18	V	
		-0.7	26		for 5 min @ 1.2 kOhm pull up
Continuous Output	Ι <sub>Q</sub>	-50	+50	mA	
Current					
Junction Temperature	Τ <sub>i</sub>	-	155	С°	for 2000 h (not additive)
	,		165		for 1000 h (not additive)
			175		for 168 h (not additive)
			195		for 3x1 h (additive)
Storage Temperature	Τs	-40	150	°C	
Magnetic Flux Density	В	-	unlimit.	тT	

Note: Stresses above those listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### **ESD** Protection

Human Body Model (HBM) tests according to: EOS/ESD Association Standard S5.1-1993 and Mil. Std. 883D method 3015.7

Parameter	Symbol	max.	Unit	Conditions
ESD Voltage	$V_{ESD}$	± 6	kV	HBM, R= 1.500 Ohm, C= 100pF; T <sub>A</sub> = 25°C

### **Operating Range**

Parameter	Symbol	min.	typ.	max.	Unit	Conditions
Supply Voltage	Vs	2.7	-	18	V	
				24		1h with $R_s >= 200 \text{ Ohm}$
				26		for 5min R <sub>s</sub> >= 200 Ohm
Output Voltage	V <sub>Q</sub>	-0.7	-	18	V	
Junction Temperature	Ti	-40	-	150	°C	
	,			175		for 168 h
Output Current	l <sub>Q</sub>	0	-	20	mA	



#### **AC/DC Characteristics**

over operating range, unless otherwise specified. Typical values correspond to Vs=12V and T<sub>A</sub>=25°C.

Parameter	Symbol	min.	typ.	max.	Unit	Conditions
Supply Current	I <sub>S</sub>	2	4	6	mA	V <sub>S</sub> = 2.7V 18V
Reverse Current	I <sub>SR</sub>	0	0.2	1	mA	V <sub>S</sub> = -18V
Output Saturation Voltage	V <sub>QSAT</sub>	-	0.3	0.6	V	I <sub>Q</sub> = 20mA
Output Leakage Current	IQ <sub>LEAK</sub>	-	0.05	10	μA	for V <sub>Q</sub> =18 V
Output Fall Time	t <sub>f</sub>	-	0.02	1	μs	R <sub>L</sub> = 1.2 kOhm ;C <sub>L</sub> =50pF
Output Rise Time	t <sub>r</sub>	-	0.4	1	μs	R <sub>L</sub> = 1.2 kOhm ;C <sub>L</sub> =50pF
Chopper Frequency	f <sub>OSC</sub>	-	320	-	kHz	
Switching Frequency	f <sub>sw</sub>	0	-	15 <sup>1)</sup>	kHz	
Delay Time <sup>2)</sup>	t <sub>d</sub>	-	13	-	μs	
Output Jitter <sup>3)</sup>	t <sub>QJ</sub>	-	1	-	μs <sub>RMS</sub>	B = Square-Wave Signal 1kHz
Repeatability of magnetic thresholds <sup>4)</sup>	B <sub>REP</sub>	-	20	-	μT <sub>RMS</sub>	$\Delta B/\Delta t$ >12mT/ms
Power-On Time <sup>5)</sup>	t <sub>PON</sub>	-	13	-	μs	V <sub>S</sub> >= 2.7V
Thermal Resistance <sup>6)</sup> P-SSO-3-2	R <sub>thJA</sub>	-	-	190	K/W	

<sup>1)</sup> To operate the sensor at the max. switching frequency, the value of the magnetic signal amplitude must be 1.4 times higher than for static fields. This is due to the -3dB corner frequency of the low pass filter in the signal path.

- <sup>2)</sup> Systematic delay between magnetic threshold reached and output switching.
- <sup>3)</sup> Jitter is the unpredictable deviation of the output switching delay.
- $^{4)}$  B<sub>REP</sub> is equivalent to the noise constant.
- <sup>5)</sup> Time from applying  $V_S \ge 2.7$  V to the sensor until the output state is valid. <sup>6)</sup> Thermal resistance from junction to ambient.

e.g.: V<sub>S</sub>=12.0 V, I<sub>S\_typ</sub>=4 mA, V<sub>QSAT\_typ</sub>=0.3 V, I<sub>Q</sub>=20 mA => Power Dissipation P<sub>dis</sub>=54.0 mW. In T<sub>A</sub> = T<sub>j</sub> - (R<sub>thJA</sub> \* P<sub>dis</sub>) = 175 °C - (190 K/W \* 0.054 W) =>  $T_{A}$  = 164.7 °C

#### **Magnetic Characteristics**

over operating range, unless otherwise specified. Typical values correspond to  $V_s$ =12V.

Parameter	Symbol	Tj [°C]	min.	typ.	max.	Unit	Conditions
Operate Point	B <sub>OP</sub>					mT	
TLE4946-1L	-	-40	11.3	15.4	19.5		
		25	11.0	15.0	19.0		
		150	10.5	14.3	18.1		
Release Point	B <sub>RP</sub>					mT	
TLE4946-1L		-40	-19.5	-15.4	-11.3		
		25	-19.0	-15.0	-11.0		
		150	-18.1	-14.3	-10.5		
Hysteresis	B <sub>HYS</sub>					mT	
TLE4946-1L	_	-40	-	-	-		
		25	22.0	30.0	38.0		
		150	-	-	-		
Temperature	TC					ppm/°C	
Compensation of		-	-	-350	-		
Magnetic Thresholds							

Positive magnetic fields related with south pole of magnet to the branded side of package. Note: Typical characteristics specify mean values expected over the production spread.



TLE4946-1L

## **Timing Diagram**

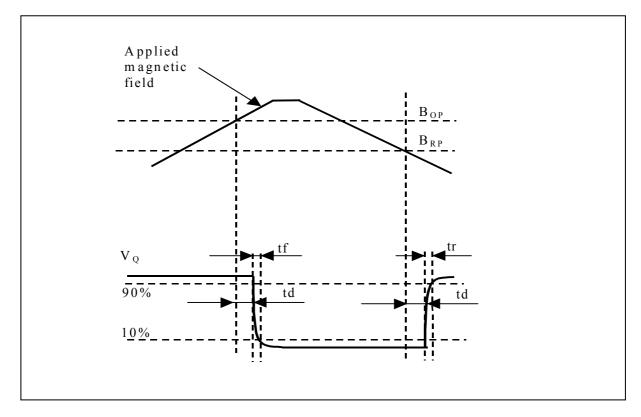


Figure 3: Timing Definition





### Package Dimension P-SSO-3-2

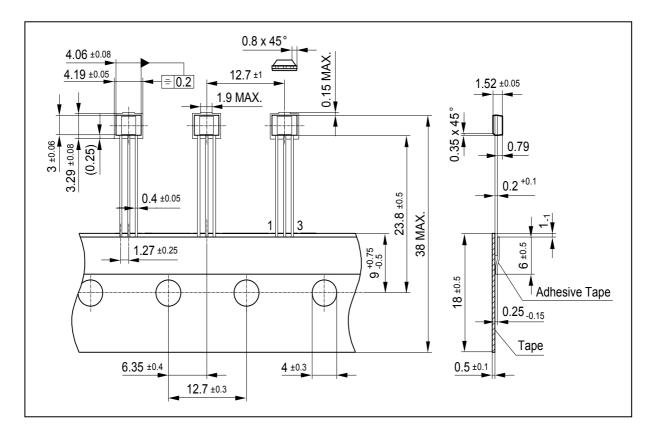


Figure 4: Package Dimension

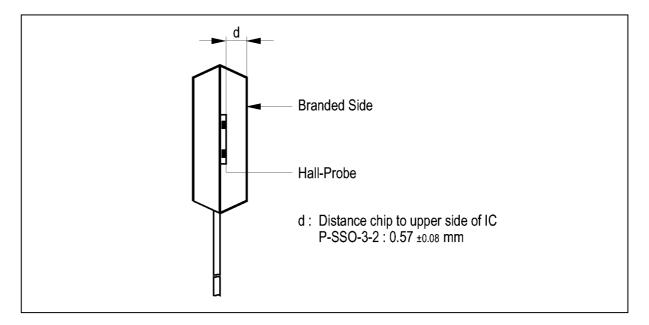


Figure 5: Distance Chip to Upper Side of IC



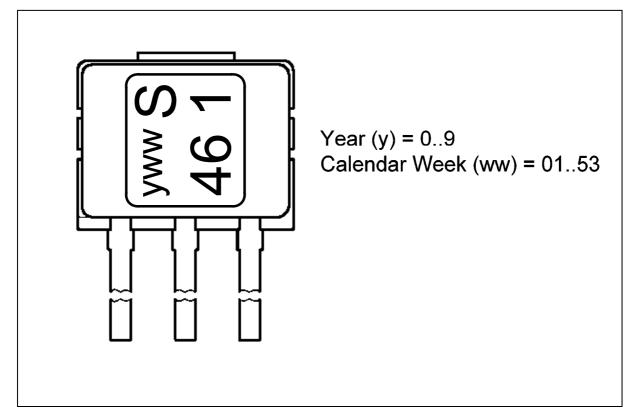


Figure 6: Marking





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Previous V	Version:	
Page	Subjects (major changes since last revision)	

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